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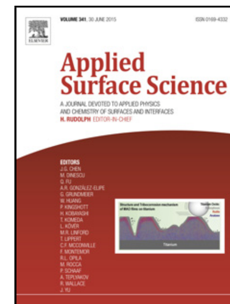

Title: Real-time spectro-ellipsometric approach to distinguish between two-dimensional Ge layer growth and Ge dot formation on SiO_2 substrates

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Real-time spectro-ellipsometric approach to distinguish between two-dimensional Ge layer growth and Ge dot formation on SiO_2 substrates

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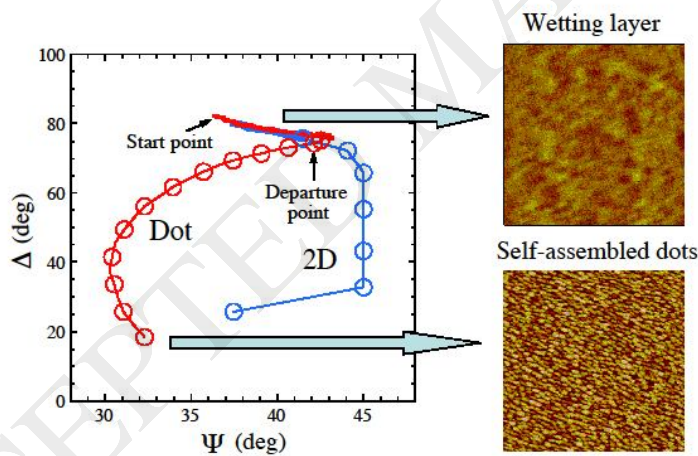
Graphical abstract



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Highlights

- Ge growth on SiO_2 was investigated by spectroscopic ellipsometry and AFM.
- 2D and 3D growth modes can be identified at an early stage by Ψ-Δ trajectory shapes.

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